

P-Ch 60V Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary



BVDSS	RDS(on)	ID
-60V	38mΩ	-30A

Description

The XR30P06 is the high cell density trenched P-ch MOSFETs, which provide excellent RDS(on) and gate charge for most of the synchronous buck converter applications.

The XR30P06 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO252-3L Pin Configuration

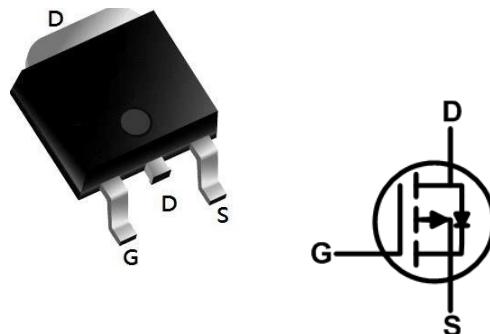


Table 1. Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0\text{V}$)	-60	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0\text{V}$)	± 20	V
I_D	Drain Current-Continuous($T_c=25^\circ\text{C}$)	-30	A
	Drain Current-Continuous($T_c=100^\circ\text{C}$)	-25.5	A
I_{DM} (pulse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	-144	A
P_D	Maximum Power Dissipation($T_c=25^\circ\text{C}$)	79	W
	Maximum Power Dissipation($T_c=100^\circ\text{C}$)	39.5	W
E_{AS}	Avalanche energy (Note 2)	196	mJ
T_J , T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		1.9	°C/W

Table 3. Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

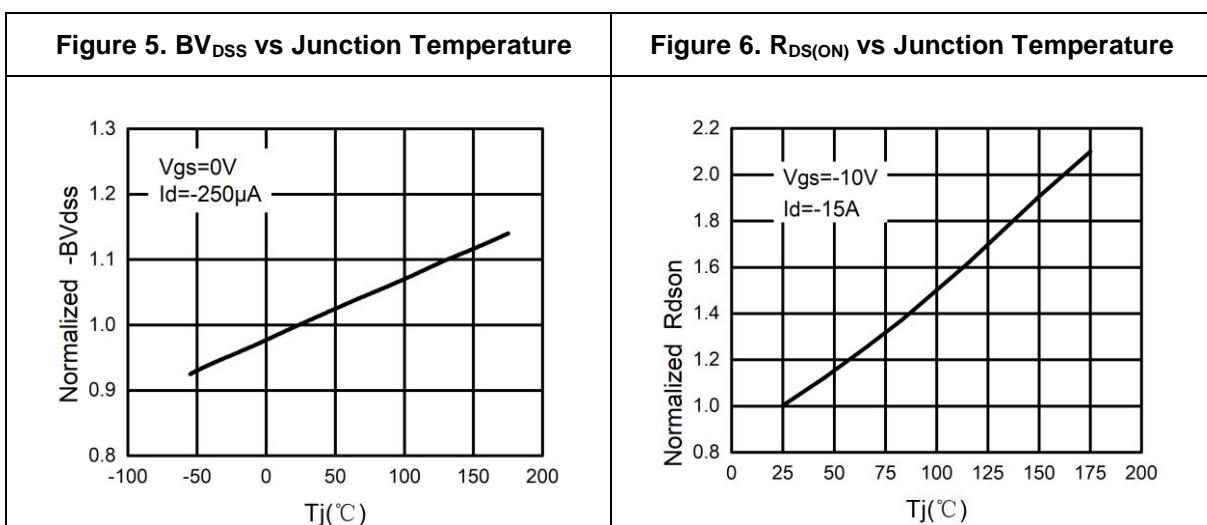
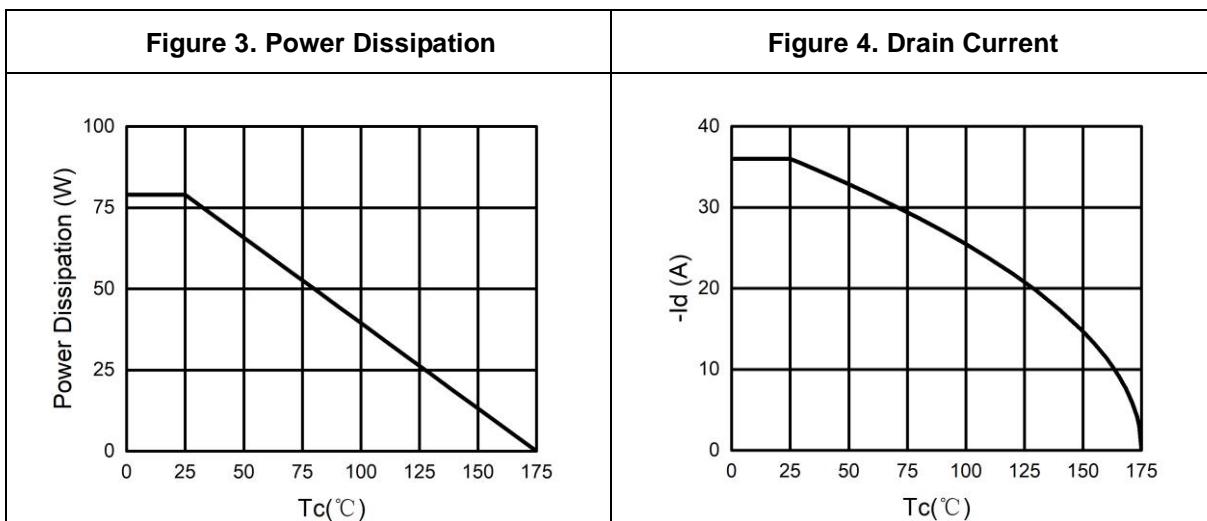
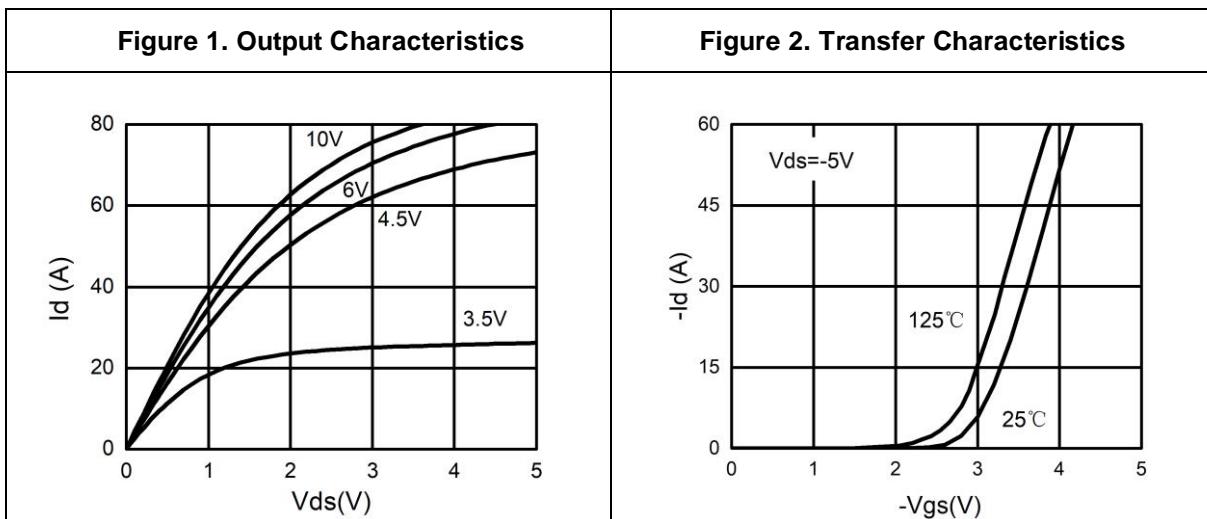
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$ $I_{\text{D}}=-250\mu\text{A}$	-60			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=-60\text{V}$, $V_{\text{GS}}=0\text{V}$			-1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$			± 100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$, $I_{\text{D}}=-250\mu\text{A}$	-1.5	-2.4	-3.5	V
g_{FS}	Forward Transconductance	$V_{\text{DS}}=-5\text{V}$, $I_{\text{D}}=-15\text{A}$		35		S
$R_{\text{DS(ON)}}$	Drain-Source On-State Resistance	$V_{\text{GS}}=-10\text{V}$, $I_{\text{D}}=-15\text{A}$		38	50	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}$, $I_{\text{D}}=-10\text{A}$		49	65	$\text{m}\Omega$
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{\text{DS}}=-25\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1.0\text{MHz}$		2616		pF
C_{oss}	Output Capacitance			87		pF
C_{rss}	Reverse Transfer Capacitance			64		pF
Switching Parameters						
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{GS}}=-10\text{V}$, $V_{\text{DS}}=-30\text{V}$, $R_{\text{L}}=1.5\Omega$, $R_{\text{GEN}}=3\Omega$		8.1		nS
t_{r}	Turn-on Rise Time			0.65		nS
$t_{\text{d(off)}}$	Turn-Off Delay Time			42		nS
t_{f}	Turn-Off Fall Time			9.1		nS
Q_{g}	Total Gate Charge	$V_{\text{GS}}=-10\text{V}$, $V_{\text{DS}}=-30\text{V}$, $I_{\text{D}}=-20\text{A}$		44		nC
Q_{gs}	Gate-Source Charge			6.8		nC
Q_{gd}	Gate-Drain Charge			8.5		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				30	A
V_{SD}	Forward on Voltage ^(Note 3)	$V_{\text{GS}}=0\text{V}$, $I_{\text{S}}=-15\text{A}$			-1.2	V
t_{rr}	Reverse Recovery Time	$I_{\text{F}}=-20\text{A}$, $d\text{i}/dt=100\text{A}/\mu\text{s}$		17		ns
Q_{rr}	Reverse Recovery Charge	$I_{\text{F}}=-20\text{A}$, $d\text{i}/dt=100\text{A}/\mu\text{s}$		19		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

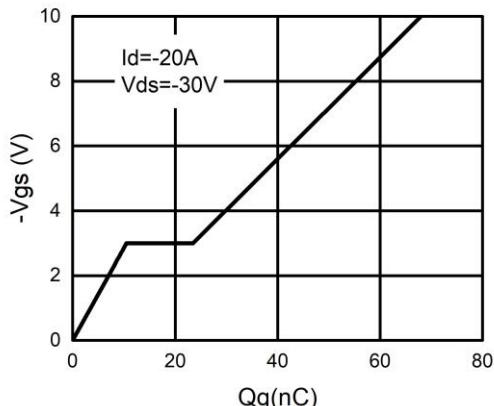
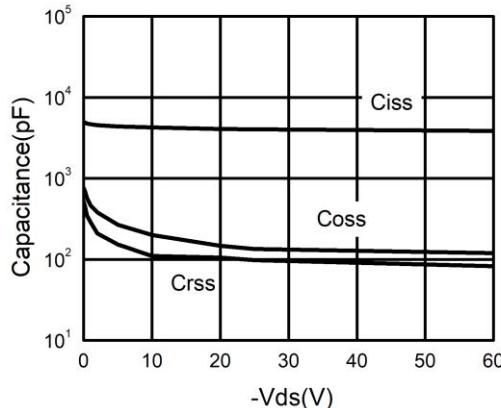
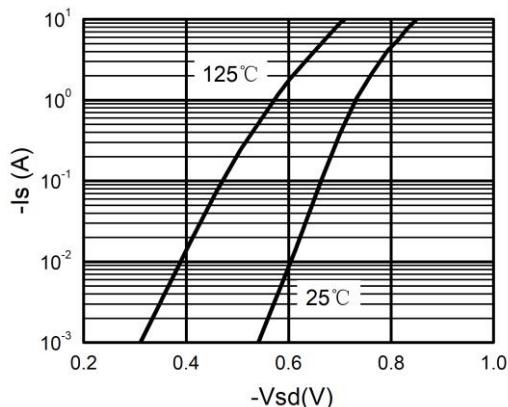
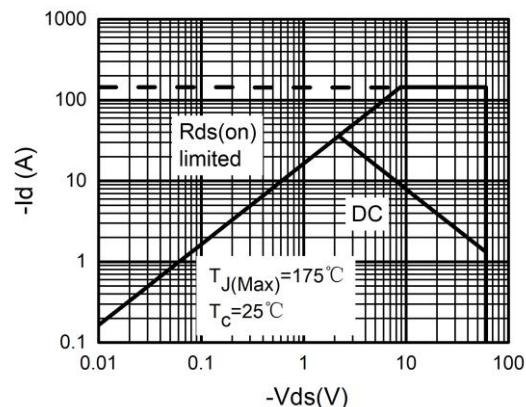
Notes 2. E_{AS} condition: $T_J=25^\circ\text{C}$, $V_{\text{DD}}=40\text{V}$, $V_{\text{G}}=-10\text{V}$, $R_{\text{G}}=25\Omega$, $L=0.5\text{mH}$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

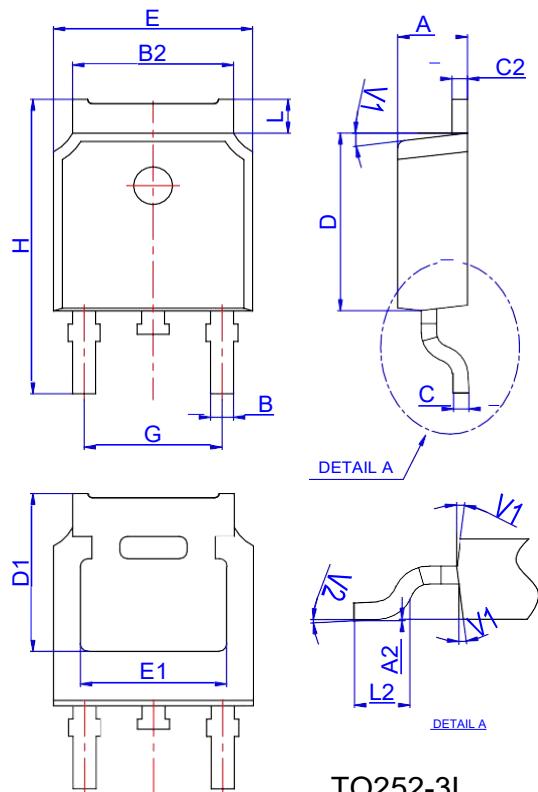
Typical Electrical And Thermal Characteristics (Curves)



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Figure 7. Gate Charge Waveforms**Figure 8. Capacitance****Figure 9. Body-Diode Characteristics****Figure 10. Maximum Safe Operating Area**

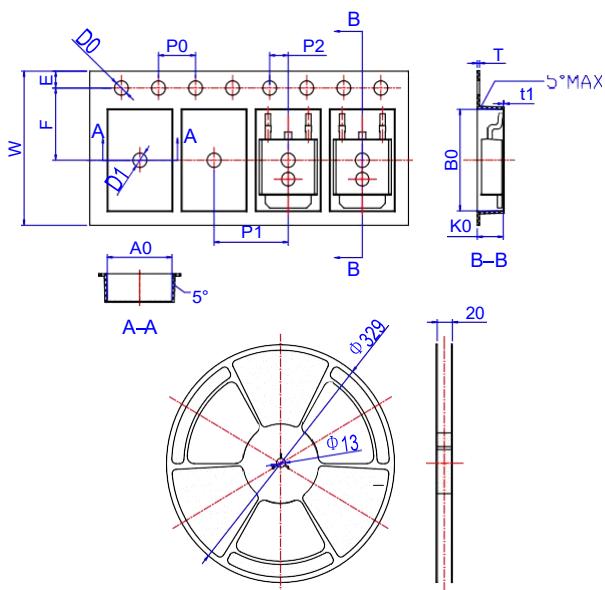
Package Mechanical Data TO252-3L



TO252-3L

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10PO	39.80	40.00	40.20	1.567	1.575	1.583